README- Isotropic Atomic Layer Etching of GaN using SF6 plasma and Al(CH3)3

Data is separated into sections:

* DFT
* Saturation curves
* Temperature
* XPS
* XRD

**DFT**

Contains the values used in Figure 2 which are the output from the Schrödinger Suites packages Jaguar and Quantum ESPRESSO.

**Saturation Curves**

Contains the thickness data derived from spectroscopic ellipsometry used in Figure 5 & 6, plus the roughness data from AFM measurements for Figure 8 & 9 in the expanded folder.

**Temperature**

Spectroscopic ellipsometry data from ALE runs performed at different temperatures, from which the EPC is calculated. These are then plotted alongside data taken from literature in Figure 7.

**XPS**

Depth profile data is given for the starting film which is reported in Figure 3. XPS data is also provided for the surface composition before and after ALE cycles, which is reported in Figure 10. The depth profile data for all the etched films is also provided and reported in the supplementary information. The subfolder of this section contains the Al content as a function of temperature data which is reported in Figure 11.

**XRD**

Data for Figure S2 showing the (002) crystal orientation of the poly crystalline GaN film.